

General Description:

The LWS6016A8 uses advanced SGT technology and design to provide excellent $R_{DS(ON)}$ with low gate charge. It can be used in a wide variety of applications. The package form is TO-220AB, which accords with the ROHS standard and Halogen Free standard.

Features:

- Fast Switching
- Low Gate Charge and $R_{DS(ON)}$
- Low Reverse transfer capacitances

Applications:

- Battery switching application
- Hard switched and high frequency circuits
- Power Management

100% DVDS Tested

100% Avalanche Tested



Package Marking and Ordering Information:

Marking	Part Number	Package	Packing	Qty.
S6016/LW A8/D.C.	LWS6016A8	TO-220AB	Tube	50Pcs

Absolute Maximum Ratings:

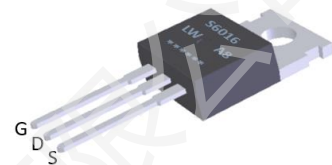
Symbol	Parameter		Value	Units
V_{DSS}	Drain-to-Source Voltage		-60	V
I_D	Continuous Drain Current	$T_C=25^{\circ}C$	-80	A
	Continuous Drain Current	$T_C=100^{\circ}C$	-51	A
I_{DM}^{a1}	Pulsed Drain Current		-320	A
V_{GS}	Gate-to-Source Voltage		± 20	V
P_D	Power Dissipation		156	W
E_{AS}^{a2}	Single pulse avalanche energy		338	mJ
T_J, T_{STG}	Operating Junction and Storage Temperature Range		150, -55 to 150	$^{\circ}C$
T_L	Maximum Temperature for Soldering		260	$^{\circ}C$

Thermal Characteristics:

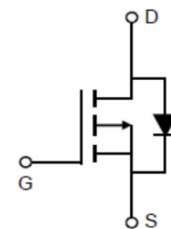
Symbol	Parameter	Value	Units
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case	0.8	$^{\circ}C/W$

V_{DSS}	-60	V
I_D	-80	A
P_D	156	W
$R_{DS(ON) \text{ TYPE}}$	11	m Ω

Marking and Pin Assignment



Inner Equivalent Principium Chart



Electrical Characteristic ($T_A = 25\text{ }^{\circ}\text{C}$, unless otherwise specified):

Static Characteristics						
Symbol	Parameter	Test Conditions	Value			Units
			Min.	Typ.	Max.	
V_{DSS}	Drain to Source Breakdown Voltage	$V_{GS}=0V, I_D=-250\mu A$	-60	--	--	V
I_{DSS}	Drain to Source Leakage Current	$V_{DS}=-60V, V_{GS}=0V$	--	--	-1.0	μA
$I_{GSS(F)}$	Gate to Source Forward Leakage	$V_{GS}=-20V, V_{DS}=0V$	--	--	-100	nA
$I_{GSS(R)}$	Gate to Source Reverse Leakage	$V_{GS}=+20V, V_{DS}=0V$	--	--	100	nA
$V_{GS(TH)}$	Gate Threshold Voltage	$V_{DS}=V_{GS}, I_D=-250\mu A$	-1.3	-1.8	-2.3	V
$R_{DS(ON)1}$	Drain-to-Source On-Resistance	$V_{GS}=-10V, I_D=-20A$	--	11	16	$m\Omega$
$R_{DS(ON)2}$	Drain-to-Source On-Resistance	$V_{GS}=-4.5V, I_D=-10A$	--	14	20	$m\Omega$

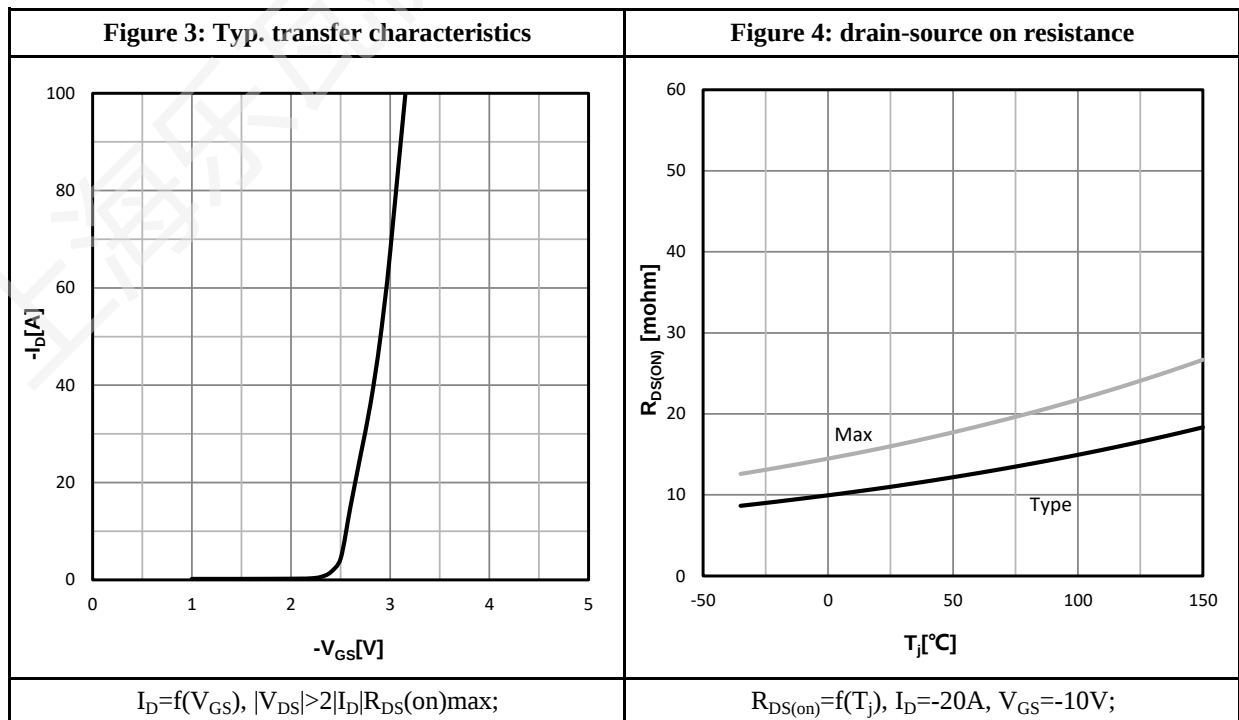
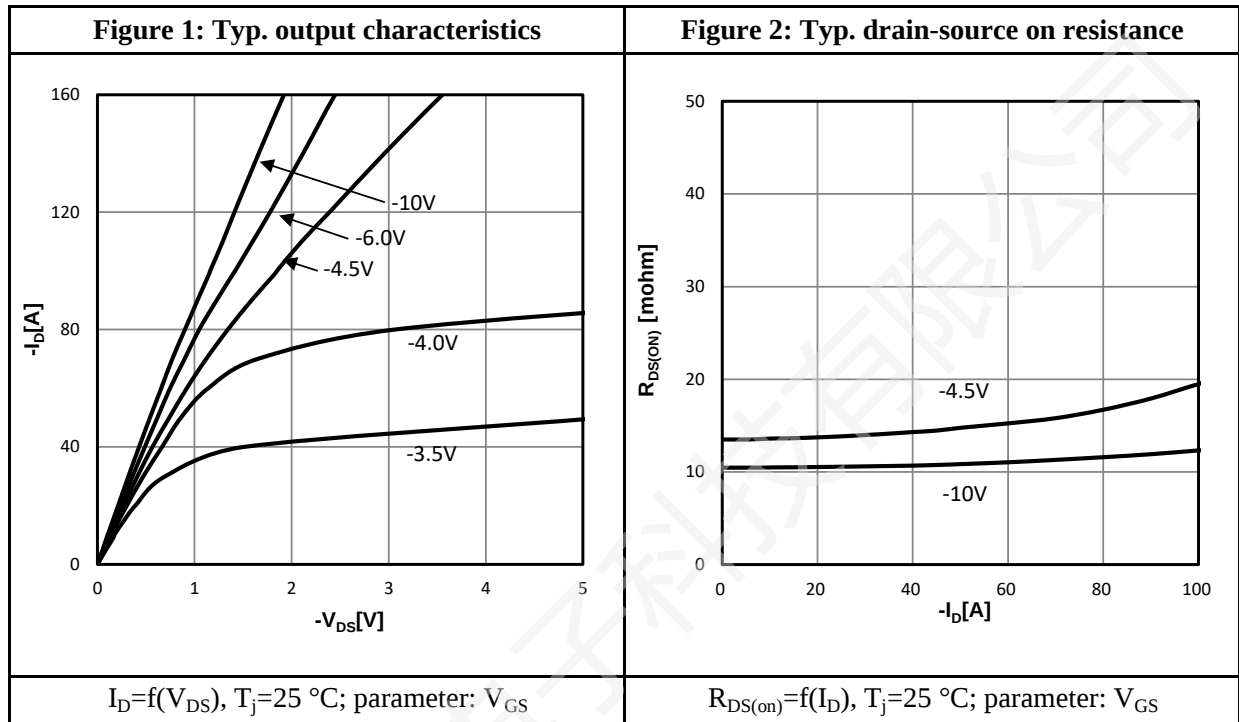
Dynamic Characteristics						
Symbol	Parameter	Test Conditions	Value			Units
			Min.	Typ.	Max.	
C_{iss}	Input Capacitance	$V_{GS} = 0V$	--	2630	--	pF
C_{oss}	Output Capacitance	$V_{DS} = -30V$	--	484	--	
C_{rss}	Reverse Transfer Capacitance	$f = 1.0MHz$	--	9.4	--	
R_G	Gate resistance	$V_{GS}=0V, V_{DS}=0V, f=1MHz$	--	12.5	--	Ω

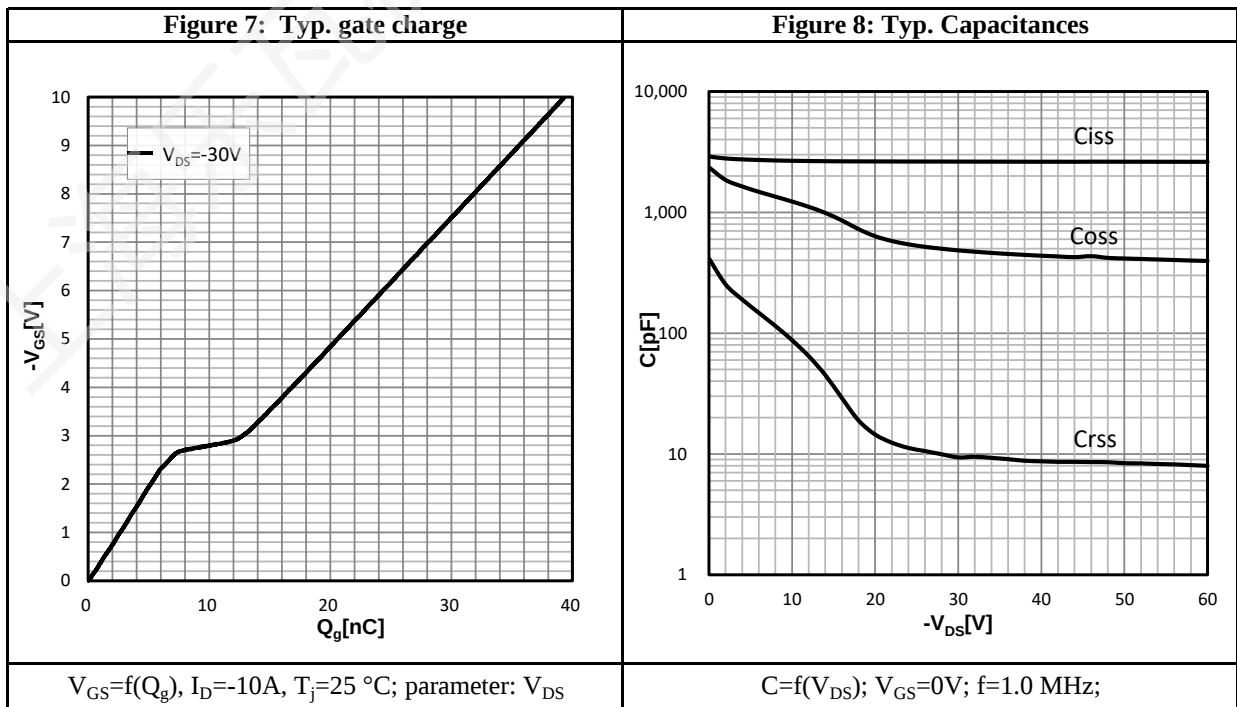
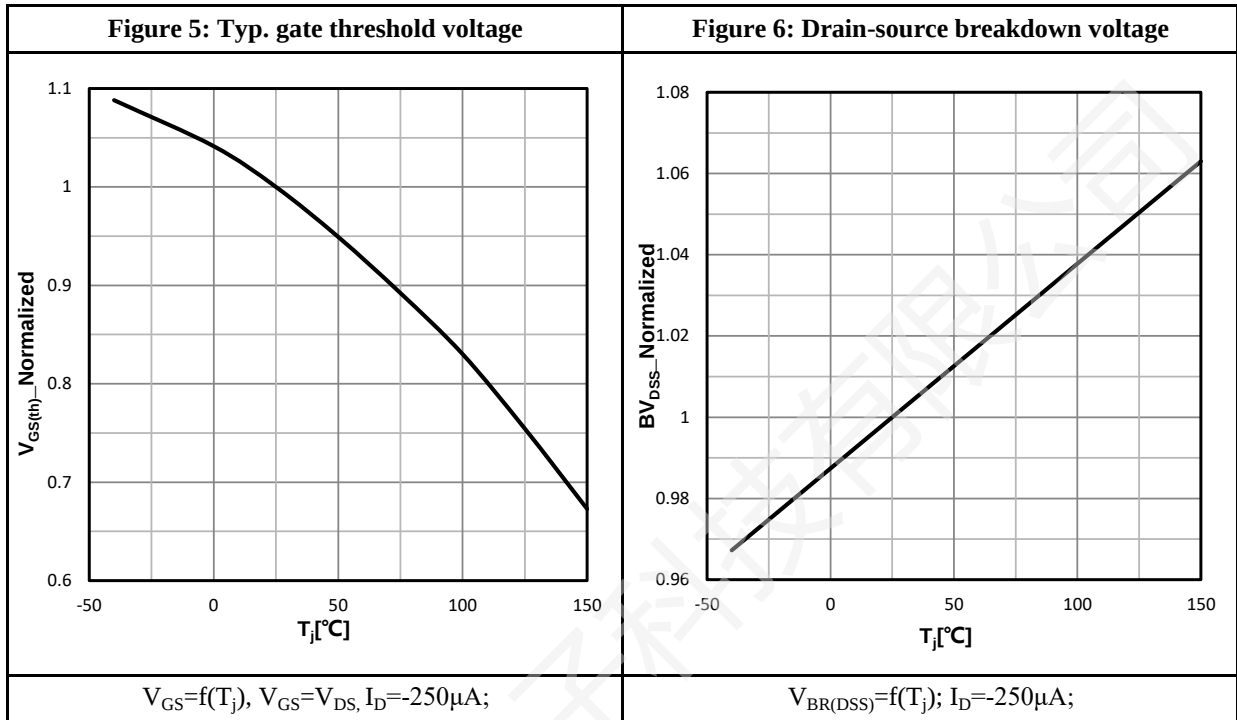
Resistive Switching Characteristics						
Symbol	Parameter	Test Conditions	Value			Units
			Min.	Typ.	Max.	
$t_{d(ON)}$	Turn-on Delay Time	$I_D = -10A$	--	20	--	ns
t_r	Rise Time	$V_{DS} = -30V$	--	25	--	
$t_{d(OFF)}$	Turn-Off Delay Time	$V_{GS} = -10V$	--	60	--	
t_f	Fall Time	$R_G = 3.0\Omega$	--	30	--	
Q_g	Total Gate Charge	$V_{GS} = -10V$	--	39	--	nC
Q_{gs}	Gate Source Charge	$V_{DS} = -30V$	--	6.9	--	
Q_{gd}	Gate Drain Charge	$I_D = -10A$	--	5.0	--	

Source-Drain Diode Characteristics						
Symbol	Parameter	Test Conditions	Value			Units
			Min.	Typ.	Max.	
I_S	Diode Forward Current	$T_C = 25\text{ }^{\circ}\text{C}$	--	--	-80	A
I_{SM}	Diode Pluse Current		--	--	-320	A
V_{SD}	Diode Forward Voltage	$I_S = -20A, V_{GS} = 0V$	--	--	-1.2	V

a1: Repetitive rating; pulse width limited by maximum junction temperature

a2: $V_{DD} = -30V, L = 1.0mH, R_G = 25\Omega$, Starting $T_j = 25\text{ }^{\circ}\text{C}$

Characteristics Curve:




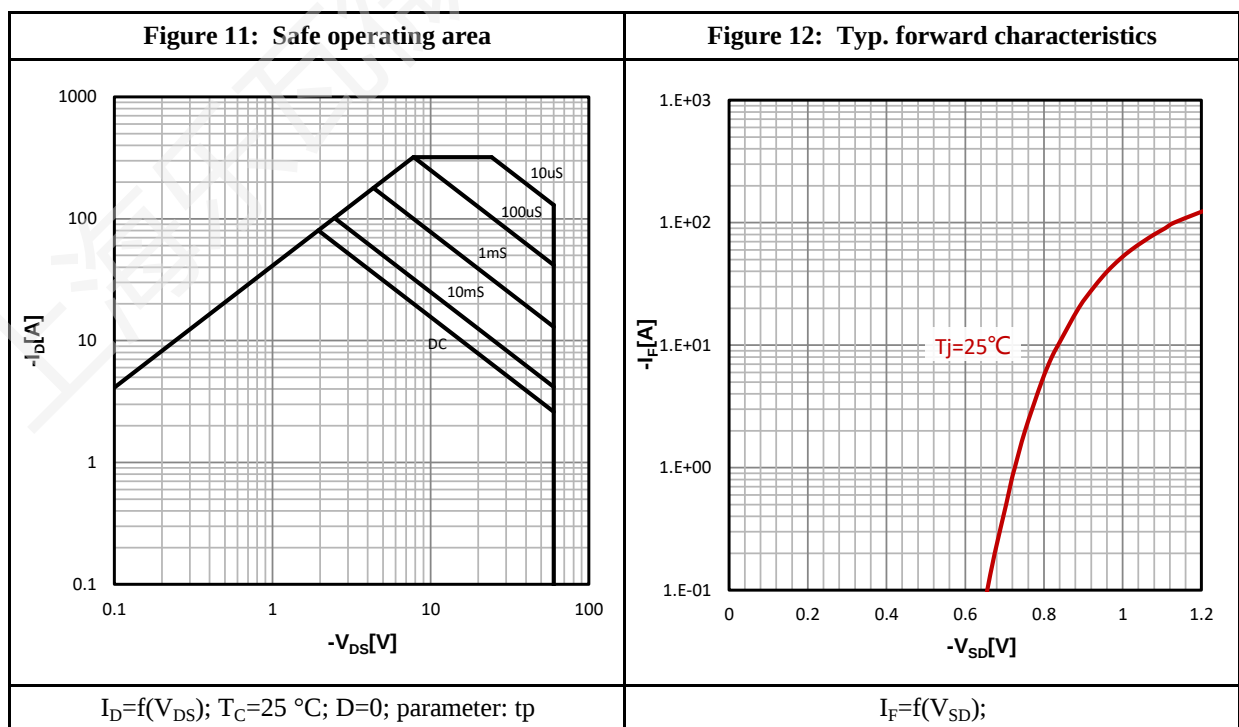
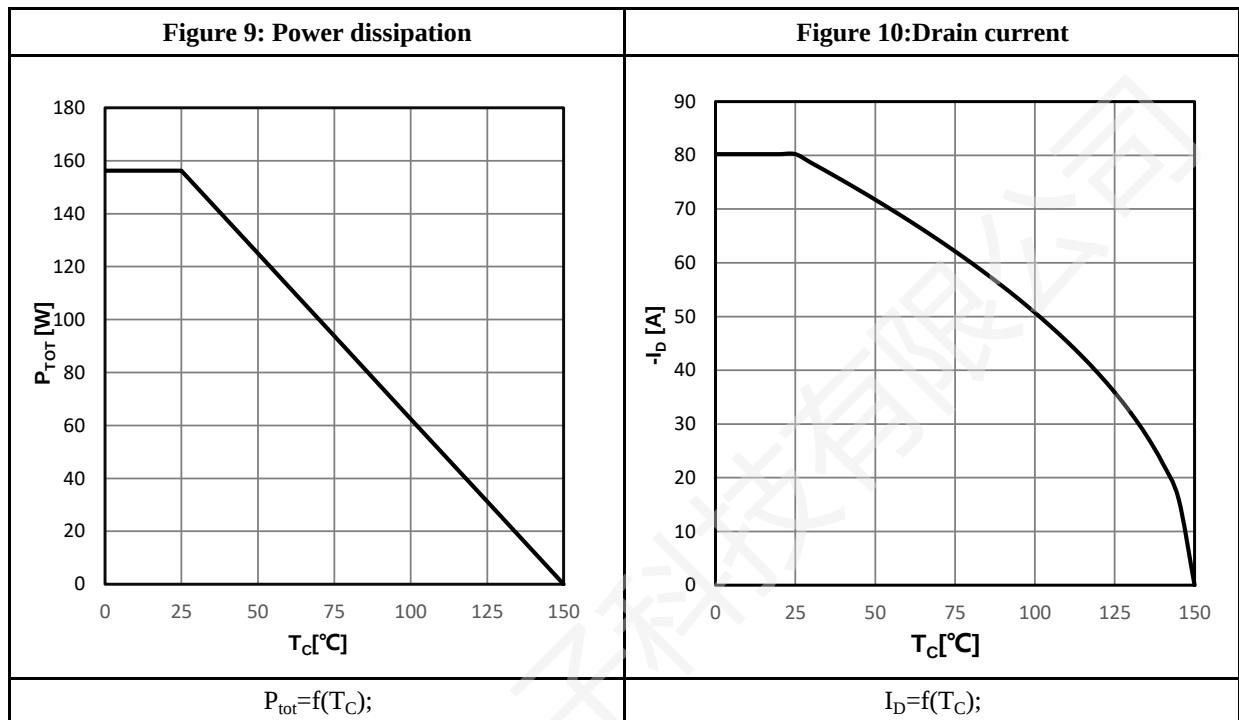
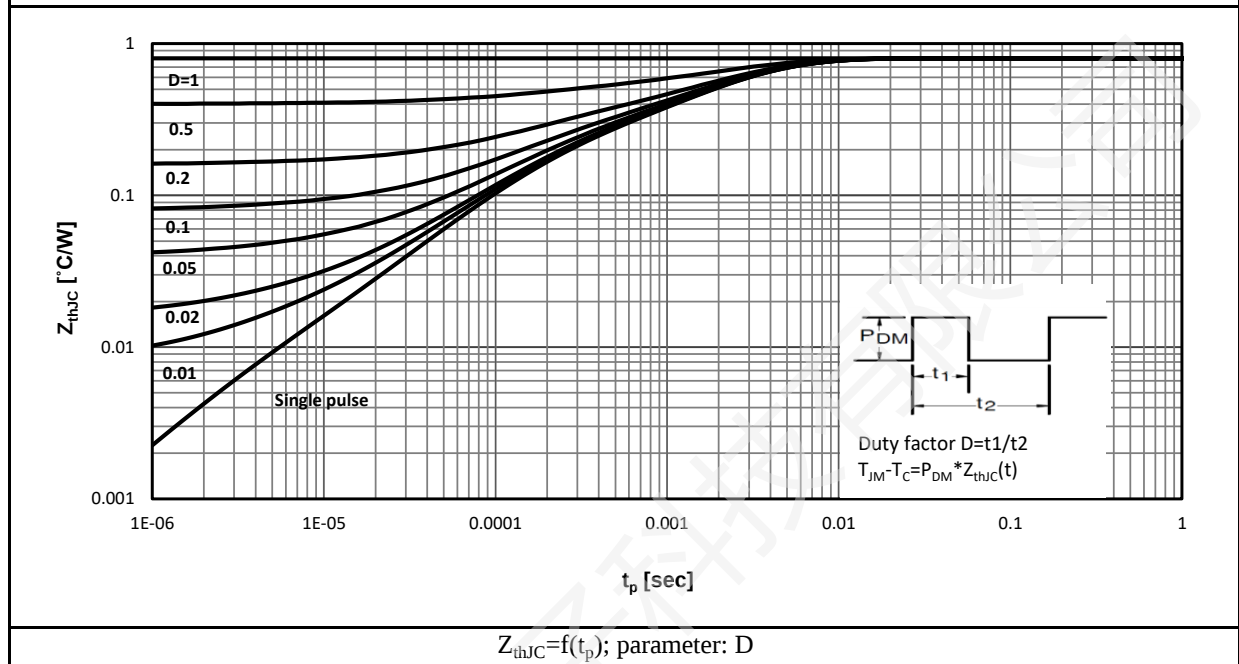
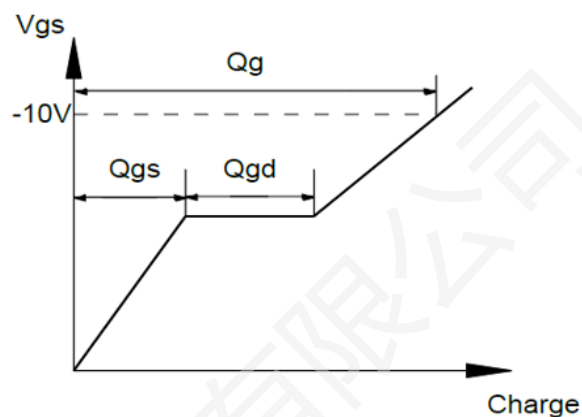
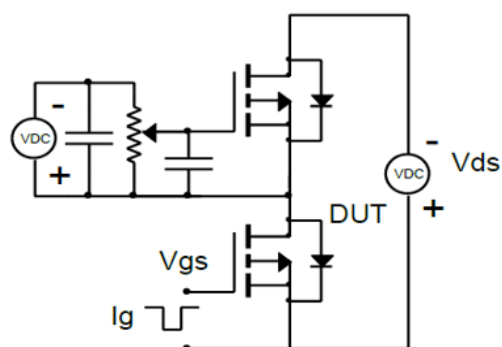
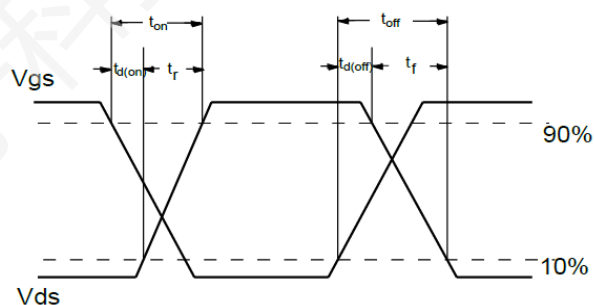
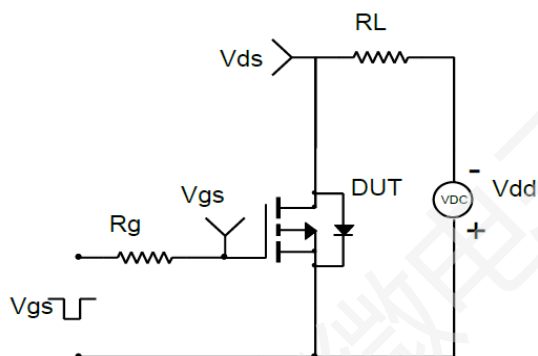
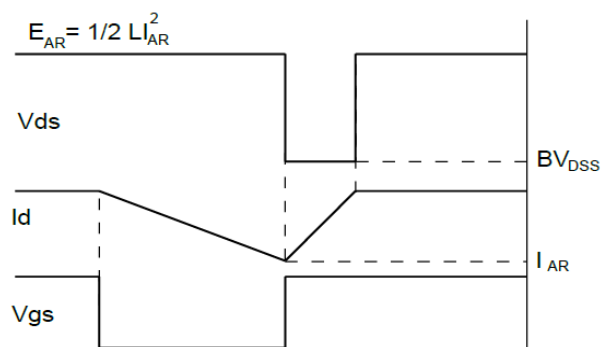
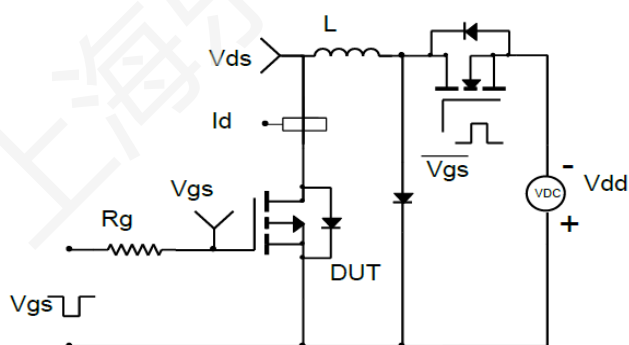
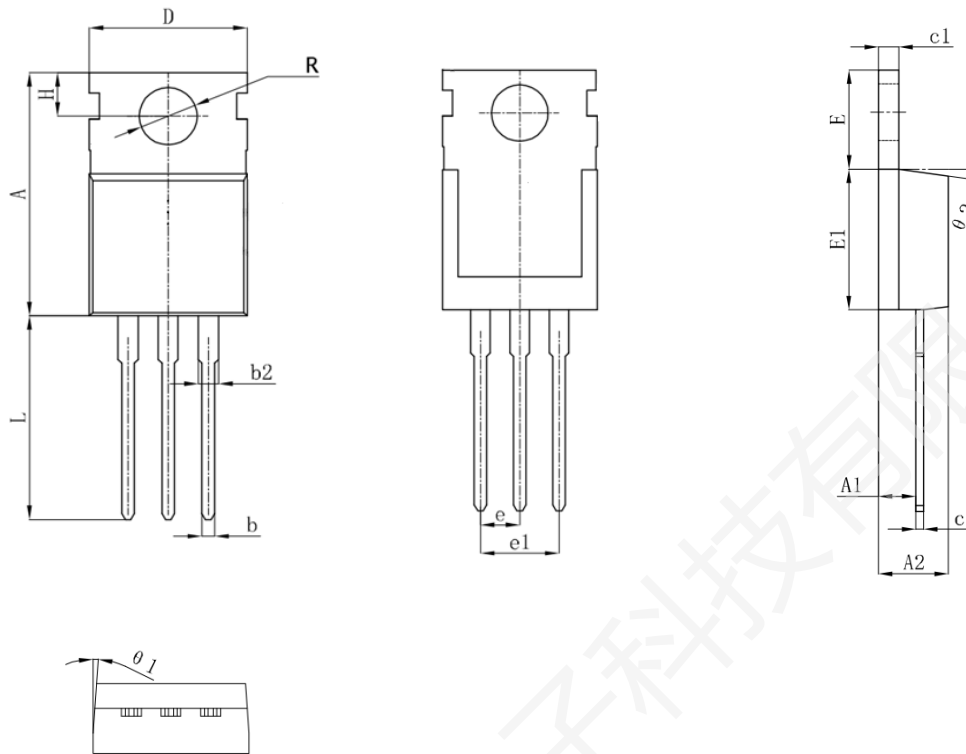


Figure 13: Max. Transient Thermal Impedance


Test Circuit & Waveform:

Figure 14: Gate Charge Test Circuit & Waveform

Figure 15: Resistive Switching Test Circuit & Waveforms

Figure 16: Unclamped Inductive Switching Test Circuit & Waveforms

Package Outline:


SYMBOL	MILLIMETER		
	MIN	NOM	MAX
A	15.3	15.55	15.8
A1	2.3	2.4	2.5
A2	4.4	4.5	4.7
b	0.7	0.8	0.9
b2	1.18	1.31	1.44
c	0.44	0.5	0.56
c1	1.28	1.3	1.33
D	9.8	10	12.2
E	6.4	6.5	6.6
E1	8.9	9.05	9.2
e	2.42	2.54	2.66
e1	4.84	5.08	5.32
H	2.73	2.8	2.87
H1	2.4	2.5	2.6
L	13.02	13.42	13.82
R	3.5	3.6	3.63
θ1	2°	2.5°	3°
θ2	6.5°	7°	7.5°

Revision History:

Revison	Date	Descriptions
Rev 1.0	May.2023	Initial Version

Disclaimer:

The information in this document is believed to be accurate and reliable. However, no responsibility is assumed by LW-Micro for its use. All operating parameters must be designed, validated and tested to ensure they meet the requirements of your application. LW-Micro reserves the right to make any specification and/or circuitry changes without prior notification. Before starting a brand-new project, please contact LW-Micro Sales to get the most recent relevant information.

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